

**SPECIFICATION AMENDMENTS:**

Please replace the paragraph bridging pages 1 and 2 with the following amended paragraph:

--Such a thin film has been heretofore formed by supplying aluminum atoms on a silicon substrate by using a sputtering method and forming an aluminum thin film so as to fill a contact hole therewith. In some cases, in the step of forming the aluminum thin film, the silicon substrate has been heated so that the contact hole can be easily filled with the aluminum thin film.--

Please replace the paragraph bridging pages 2 and 3 with the following amended paragraph:

--Further, there is another problem that in the step of forming an aluminum thin film or the following steps, aluminum atoms diffuse in diffusion regions or the like on the silicon substrate (aluminum spike) and thereby the p-n junction of a device is destructed.--

Please replace the paragraph on page 17, lines 5 through 14, with the following amended paragraph:

--Further, silicon atoms constituting the polysilicon film 15 also diffuse in the aluminum thin film 16. In such a manner, the contact hole 4 is gradually filled with the aluminum thin film 16 (see Fig. 2(c)), and at the end of the thin film formation, the contact hole 4 is wholly filled with the aluminum thin film 16. It is

possible to continue heating the silicon substrate 1 for a suitable time after stopping supplying the supply of aluminum atoms onto the silicon substrate 1.--

AMENDMENT  
Filed December 14, 2005

10/766,212